

## N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)	$Q_g$ (Typ.)
30	0.093 at $V_{GS} = 10$ V	1.3 <sup>a</sup>	5.41
	0.129 at $V_{GS} = 4.5$ V	1.2	

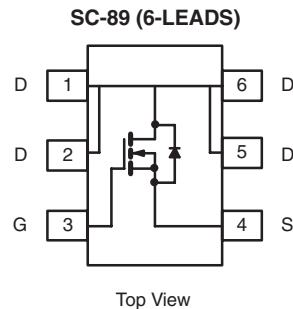
### FEATURES

- Halogen-free Option Available
- TrenchFET<sup>®</sup> Power MOSFET
- 100 %  $R_g$  and UIS Tested

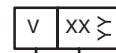

**RoHS**  
COMPLIANT

### APPLICATIONS

- Load Switch for Portable Devices



Marking Code


 Lot Traceability  
and Date Code

Part # Code

Ordering Information: Si1072X-T1-E3 (Lead (Pb)-free)  
Si1072X-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 150$ °C) <sup>a</sup>	$I_D$	$T_A = 25$ °C	1.3 <sup>b, c</sup>
		$T_A = 70$ °C	1.03 <sup>b, c</sup>
Pulsed Drain Current	$I_{DM}$	6	A
Avalanche Current	$I_{AS}$	8	
Repetitive Avalanche Energy	$E_{AS}$	3.2	mJ
Continuous Source-Drain Diode Current	$I_S$	$T_A = 25$ °C	0.2 <sup>b, c</sup>
		$T_A = 70$ °C	0.151 <sup>b, c</sup>
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_A = 25$ °C	0.236 <sup>b, c</sup>
		$T_A = 70$ °C	0.151 <sup>b, c</sup>
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>b, d</sup>	$R_{thJA}$	$t \leq 5$ s	440	530	°C/W
		Steady State	540	650	

Notes:

- Based on  $T_C = 25$  °C.
- Surface Mounted on 1" x 1" FR4 board.
- $t = 5$  s.
- Maximum under Steady State conditions is 650 °C/W.

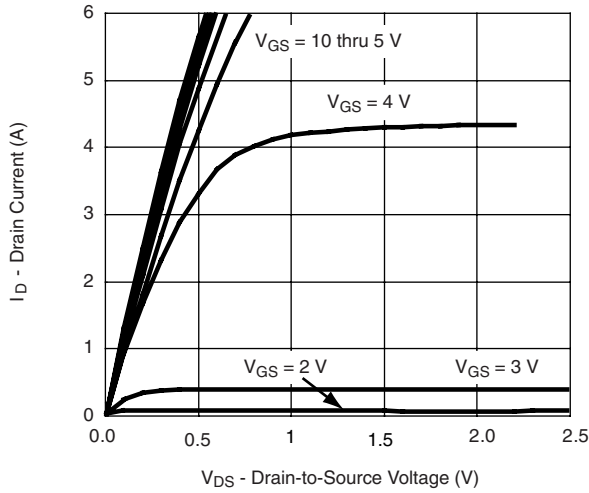
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		30.4		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 1.86		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		3	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	6			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 1.3\text{ A}$		0.077	0.093	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 1.2\text{ A}$		0.107	0.129	
Forward Transconductance	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 1.3\text{ A}$		15		mS
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		280		pF
Output Capacitance	$C_{oss}$			55		
Reverse Transfer Capacitance	$C_{rss}$			35		
Total Gate Charge	$Q_g$	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 1.3\text{ A}$		5.5	8.3	nC
				2.7	4.1	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 1.3\text{ A}$		1.1		
Gate-Drain Charge	$Q_{gd}$			0.8		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		3.5	4.6	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 13.6\text{ }\Omega$ $I_D \approx 1.1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		7	11	ns
Rise Time	$t_r$			12	18	
Turn-Off DelayTime	$t_{d(off)}$			12	18	
Fall Time	$t_f$			6	9	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 15.5\text{ }\Omega$ $I_D \approx 0.97\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		13	20	
Rise Time	$t_r$			31	47	
Turn-Off DelayTime	$t_{d(off)}$			9	14	
Fall Time	$t_f$			6	9	
<b>Drain-Source Body Diode Characteristics</b>						
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				6	A
Body Diode Voltage	$V_{SD}$	$I_S = 0.7\text{ A}$		0.8	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 1.2\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		11.2	17	nC
Body Diode Reverse Recovery Charge	$Q_{rr}$			4.5	6.8	ns
Reverse Recovery Fall Time	$t_a$			7.5		
Reverse Recovery Rise Time	$t_b$			3.7		

Notes:

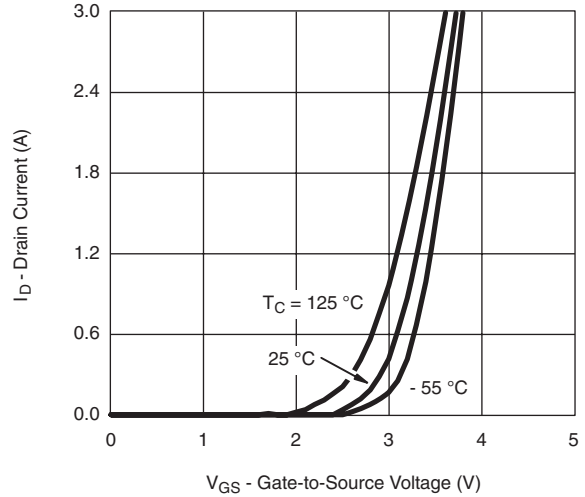
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

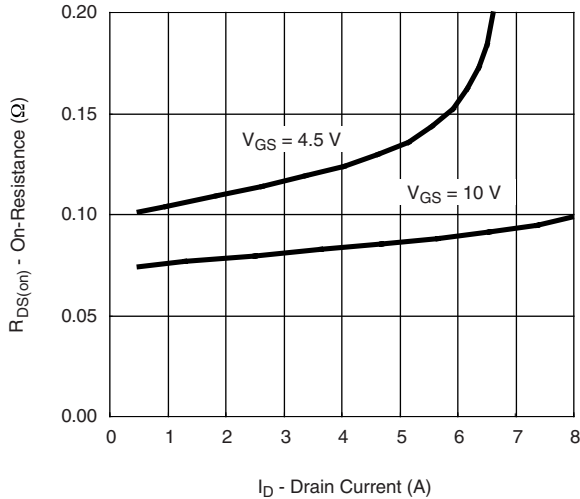
**TYPICAL CHARACTERISTICS**  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted



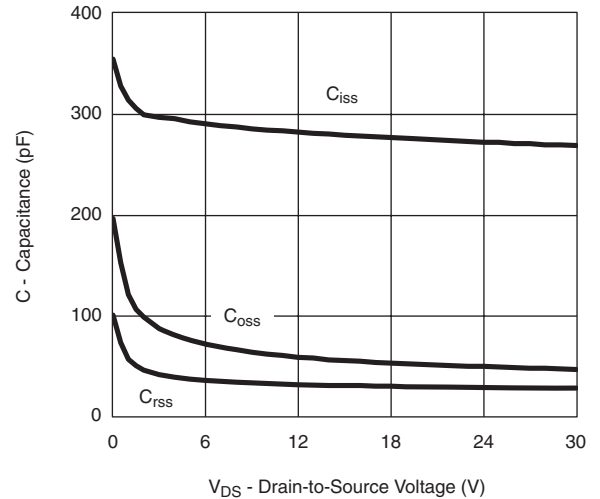
**Output Characteristics**



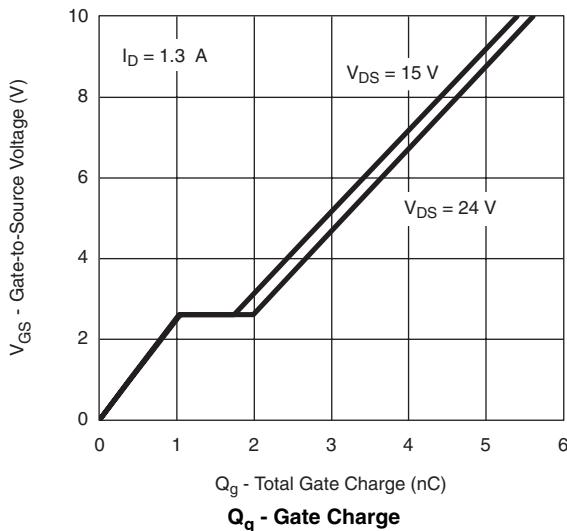
**Transfer Characteristics Curves vs. Temp.**



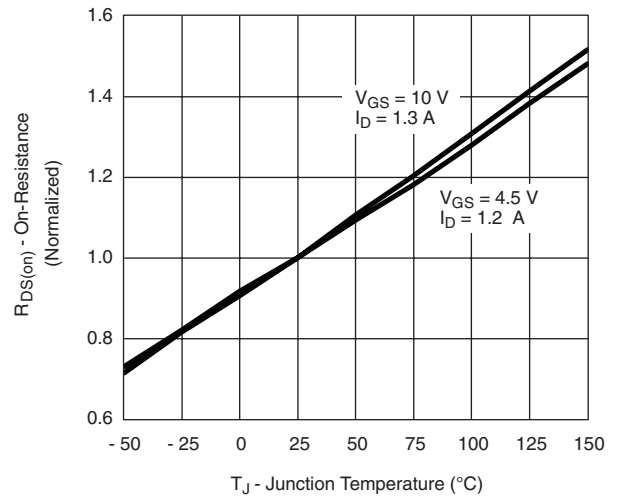
**On-Resistance vs. Drain Current**



**Capacitance**

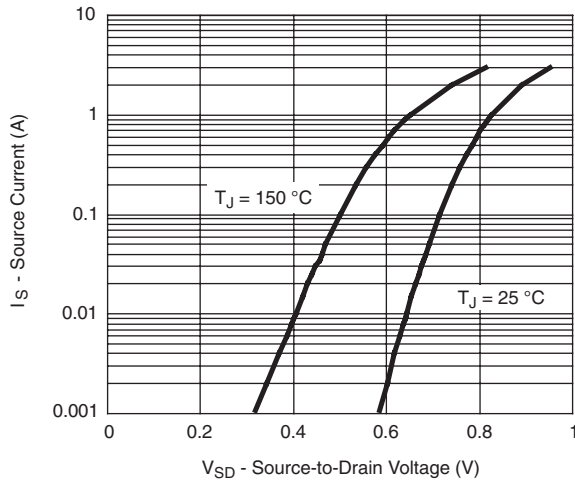


**$Q_g$  - Gate Charge**

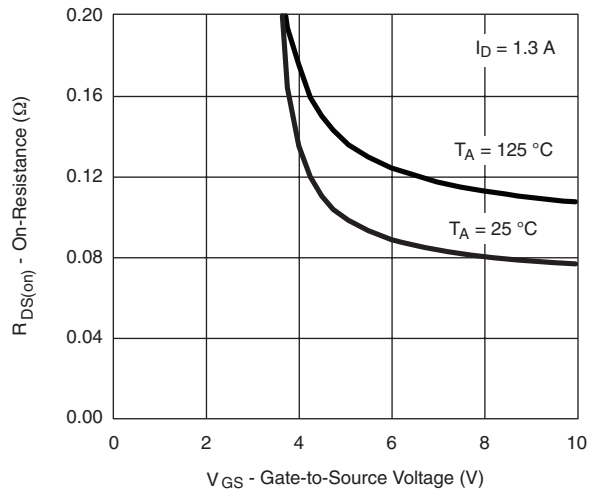


**On-Resistance vs. Junction Temperature**

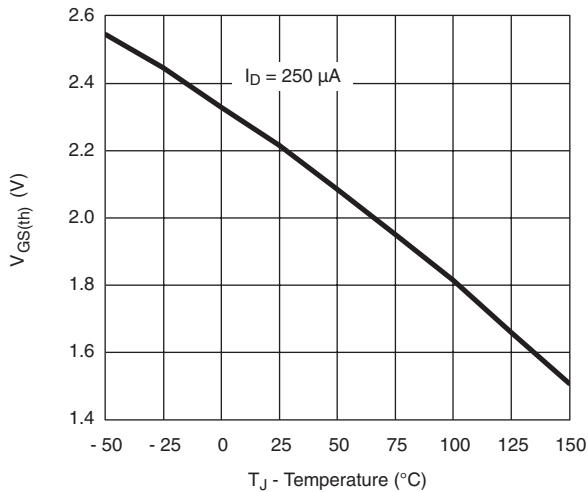
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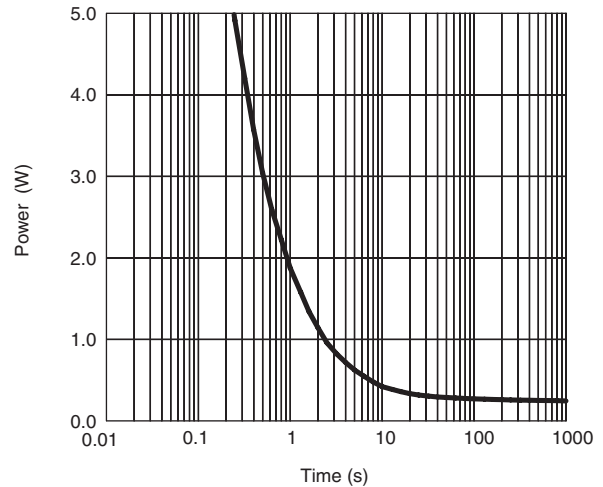
**Source-Drain Diode Forward Voltage**



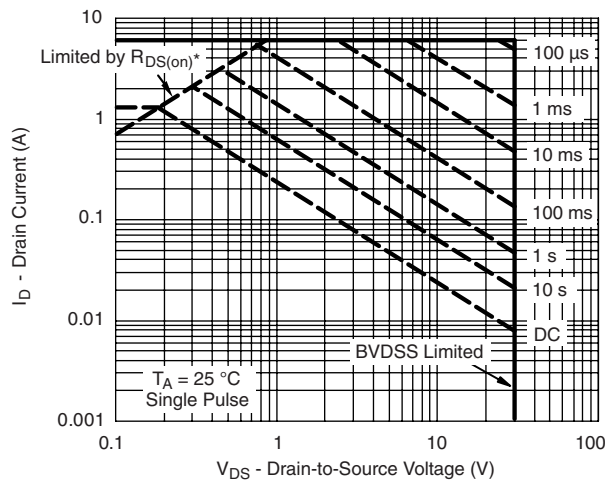
**$R_{DS(on)}$  vs.  $V_{GS}$  vs. Temperature**



**Threshold Voltage**

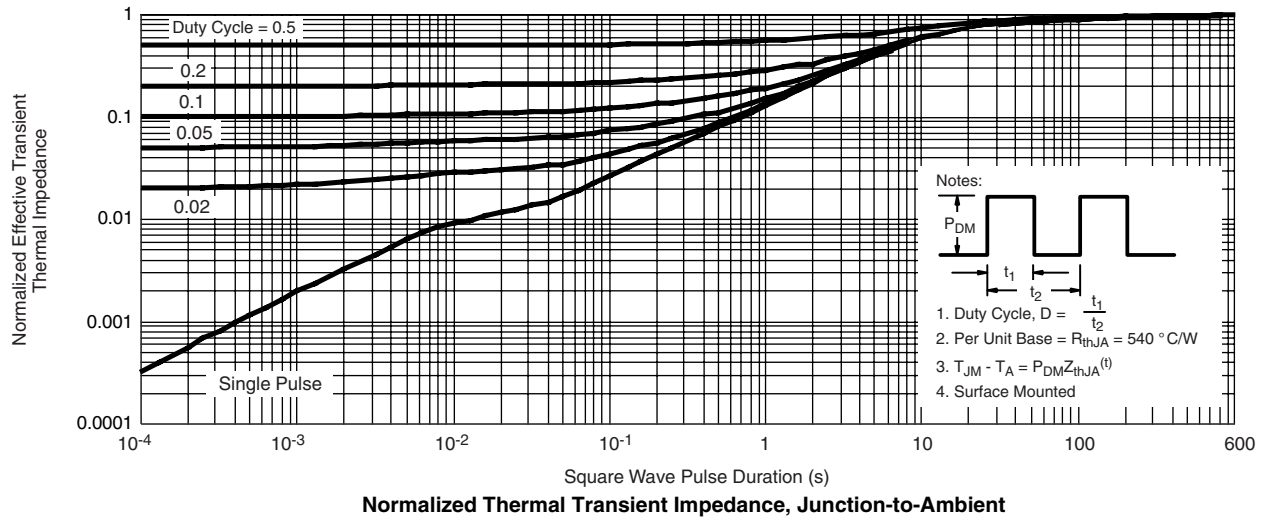


**Single Pulse Power**



**Safe Operating Area, Junction-to-Ambient**

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